

PNP TRANSISTOR**8550S****-0.5A**

TO-92

- Power Dissipation: 0.625W
- Collector Current: -0.5A
- Collector-Base Voltage: -45V

MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS ($T_a=25^\circ\text{C}$)

PARAMETERS	SYMBOL	MIN	TYP	MAX	UNIT	CONDITION
Collector-Emitter Breakdown Voltage	BV_{ce0}	-25			V	$I_c=-0.1\text{mA}$
Collector-Base Breakdown Voltage	BV_{cb0}	-45			V	$I_c=-100\mu\text{A}$
Emitter-Base Breakdown Voltage	BV_{eb0}	-5			V	$I_e=-100\mu\text{A}$
Collector-Base Leakage	I_{cbo}			-0.1	μA	$V_{cb}=-40\text{V}$
Collector-Emitter Leakage	I_{ceo}			-0.1	μA	$V_{ce}=-20\text{V}$
Emitter-Base Leakage	I_{ebo}			-0.1	μA	$V_{eb}=-5\text{V}$
Collector-Emitter Saturation Voltage	$V_{ce(sat)}$			-0.6	V	$I_c=-500\text{mA}, I_b=-50\text{mA}$
Base-Emitter Saturation Voltage	$V_{be(sat)}$			-1.2	V	$I_c=-500\text{mA}, I_b=-50\text{mA}$
DC Current Gain	H_{fe1} H_{fe2}	85 50		300		$V_{ce}=-1\text{V}, I_c=-50\text{mA}$ $V_{ce}=-1\text{V}, I_c=-500\text{mA}$
Collector Current	I_c			-0.5	A	
Peak Collector Current	I_{cp}			-8	A(Pulse)	
Current Gain Bandwidth	f_T	150			MHz	$V_{cb}=-6\text{V}, I_c=-20\text{mA}$
Output Capacitance	C_{ob}			32	pF	$V_{cb}=-20\text{V}, I_e=0, f=1\text{MHz}$
Power Dissipation	P_c			0.625	W	
Junction Temperature	T_j			150		
Storage Temperature	T_{stg}	-55		150		

Hfe1 Classification

Rank	B	C	D
Range	85-160	120-200	160-300

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